	Substitute for form 1449/PTO				Application Number	10/788,857	
0	IPE				Filing Date:	February 26, 2004	
	1	Information	Disclosure	9	First Named Inventor:	Chao I. WU	
_ FEB	FEB 0 7 2006 S Statement By Applicant			it	Art Unit:	2824	
PATER	/ہیے	(Use as many she	ets as necessary)	Examiner Name:	N. Nguyen	
137	A. T.				Attorney Docket Number:	MXICP031	
1/18	DEMISITE	1	of	1			

U.S. Patent Documents

			U.S. I atent i	Journal of the second of the 	
Examiner Initial	Cite No.	Document No.	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, where Relevant Passages or Relevant Figures Appear
	A	6,011,725	1/2000	Eitan	
	В	6,487,114	11/2002	Jong et al.	
	С				
	D				
	E				,
* '	F				
	G				
	Н				
	1				
	J				
	K				

Foreign Patent Documents

				<u> </u>			
Examiner Initial	Cite No.	Foreign Patent Document No.	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, where Relevant Passages or Relevant Figures Appear	Transla YES	ation NO
	L	-					
	M						
	N						
	0						
	Р						
	Q						

Non Patent Literature Documents

Examiner Initial	Cite No.	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
	R	T. Y. CHAN et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," IEEE Electron Device Letters, Vol. EDL-8, No. 3, March 1987, pp. 93-95
	S	
	T	
_	U	
	٧	
	W	

Examiner Signature	Date Considered
Examine Signature	Date Considered

Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.